

# MOSFET – Power, Single, N-Channel

40 V, 102 A, 3.3 mΩ

## NTMYS3D5N04C

### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- LPAK4 Package, Industry Standard
- These Devices are Pb-Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter			Value	Unit
V <sub>DSS</sub>	Drain-to-Source Voltage			40	V
V <sub>GS</sub>	Gate-to-Source Voltage			±20	V
I <sub>D</sub>	Continuous Drain Current R <sub>θJC</sub> (Notes 1, 3)	Steady State	T <sub>C</sub> = 25°C	102	A
			T <sub>C</sub> = 100°C	72	
P <sub>D</sub>	Power Dissipation R <sub>θJC</sub> (Note 1)		T <sub>C</sub> = 25°C	68	W
			T <sub>C</sub> = 100°C	34	
I <sub>D</sub>	Continuous Drain Current R <sub>θJA</sub> (Notes 1, 2, 3)	Steady State	T <sub>A</sub> = 25°C	24	A
			T <sub>A</sub> = 100°C	17	
P <sub>D</sub>	Power Dissipation R <sub>θJA</sub> (Notes 1, 2)		T <sub>A</sub> = 25°C	3.6	W
			T <sub>A</sub> = 100°C	1.8	
I <sub>DM</sub>	Pulsed Drain Current	T <sub>A</sub> = 25°C, t <sub>p</sub> = 10 μs		554	A
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature Range			-55 to +175	°C
I <sub>S</sub>	Source Current (Body Diode)			65	A
E <sub>AS</sub>	Single Pulse Drain-to-Source Avalanche Energy (I <sub>L(pk)</sub> = 7.0 A)			215	mJ
T <sub>L</sub>	Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL RESISTANCE MAXIMUM RATINGS

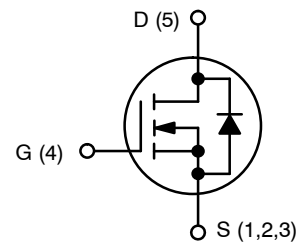
Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Junction-to-Case – Steady State	2.2	$^\circ\text{C/W}$
$R_{\theta JA}$	Junction-to-Ambient – Steady State (Note 2)	39	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	3.3 mΩ @ 10 V	102 A

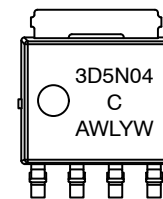


LPAK4  
CASE 760AB



N-CHANNEL MOSFET

### MARKING DIAGRAM



3D5N04C = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
W = Work Week

### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NTMYS3D5N04C

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	40			V
$V_{(BR)DSS}/T_J$	Drain-to-Source Breakdown Voltage Temperature Coefficient			22		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		10	$\mu\text{A}$
			$T_J = 125^\circ\text{C}$		100	
$I_{GSS}$	Gate-to-Source Leakage Current	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

### ON CHARACTERISTICS (Note 6)

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$V_{GS(TH)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 60\text{ }\mu\text{A}$	2.5		3.5	V
$V_{GS(TH)}/T_J$	Threshold Temperature Coefficient			-7.8		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Drain-to-Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		2.7	3.3	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 50\text{ A}$		93		S

### CHARGES, CAPACITANCES & GATE RESISTANCE

$C_{ISS}$	Input Capacitance	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$		1600		pF
$C_{OSS}$	Output Capacitance			830		
$C_{RSS}$	Reverse Transfer Capacitance			28		
$Q_{G(TOT)}$	Total Gate Charge	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 50\text{ A}$		23		nC
$Q_{G(TH)}$	Threshold Gate Charge	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 50\text{ A}$		5.1		
$Q_{GS}$	Gate-to-Source Charge			9.0		
$Q_{GD}$	Gate-to-Drain Charge			3.5		
$V_{GP}$	Plateau Voltage			5.3		V

### SWITCHING CHARACTERISTICS (Note 7)

$t_{d(ON)}$	Turn-On Delay Time	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}, R_G = 2.5\text{ }\Omega$		10		ns
$t_r$	Rise Time			47		
$t_{d(OFF)}$	Turn-Off Delay Time			19		
$t_f$	Fall Time			3.0		

### DRAIN-SOURCE DIODE CHARACTERISTICS

V <sub>SD</sub>	Forward Diode Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 50 A	T <sub>J</sub> = 25°C		0.9	1.2	V
			T <sub>J</sub> = 125°C		0.78		
t <sub>RR</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 50 A			37		ns
t <sub>a</sub>	Charge Time				18		
t <sub>b</sub>	Discharge Time				19		
Q <sub>RR</sub>	Reverse Recovery Charge				23		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

5. Switching characteristics are independent of operating junction temperatures.

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6. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

7. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

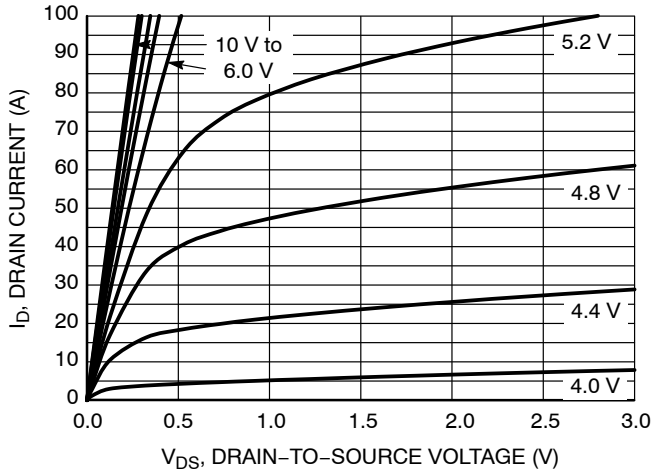


Figure 1. On-Region Characteristics

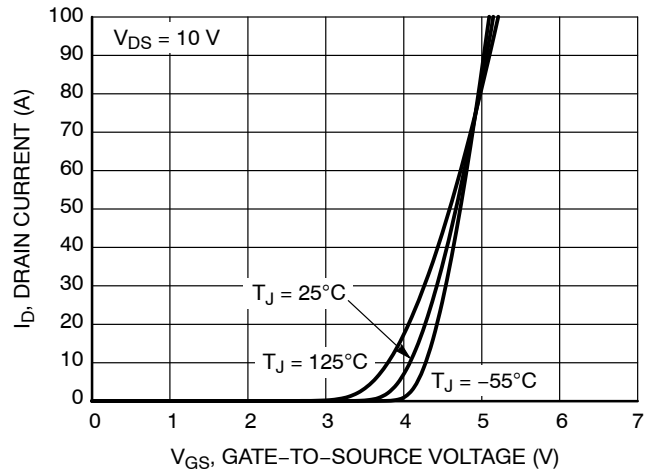


Figure 2. Transfer Characteristics

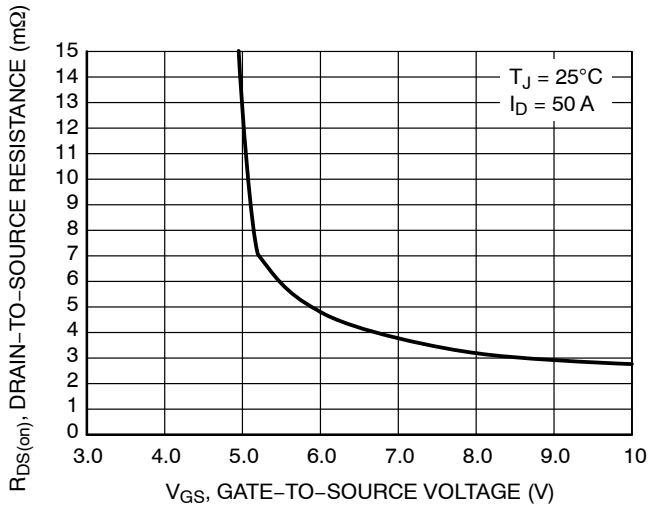


Figure 3. On-Resistance vs. Gate-to-Source Voltage

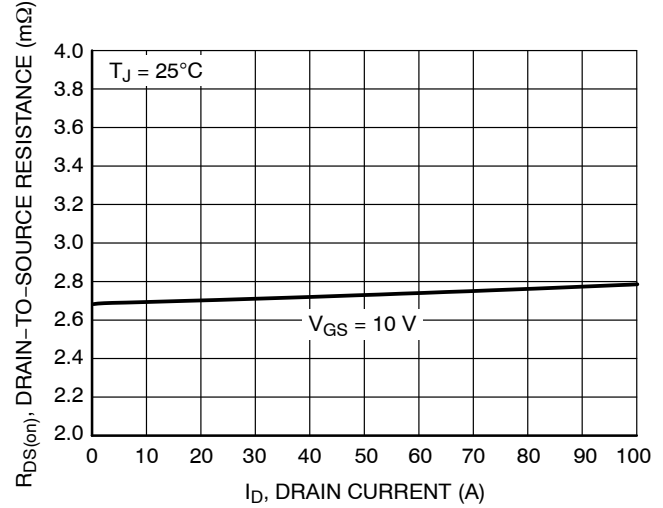


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

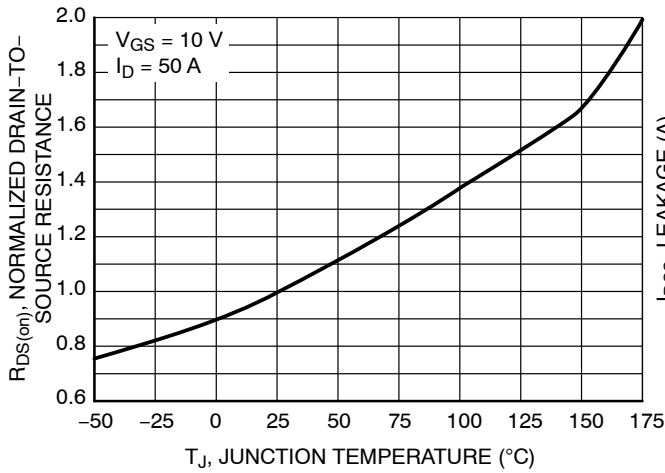


Figure 5. On-Resistance Variation with Temperature

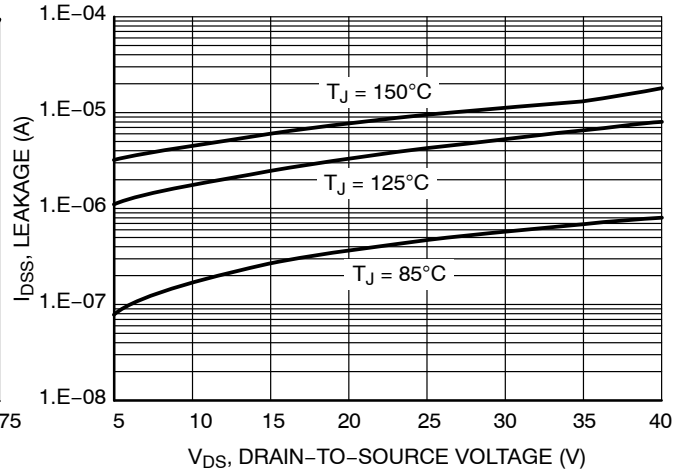


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS (continued)

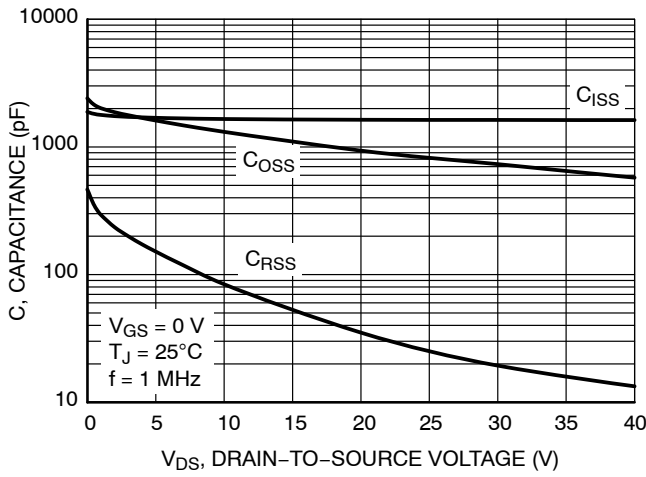


Figure 7. Capacitance Variation

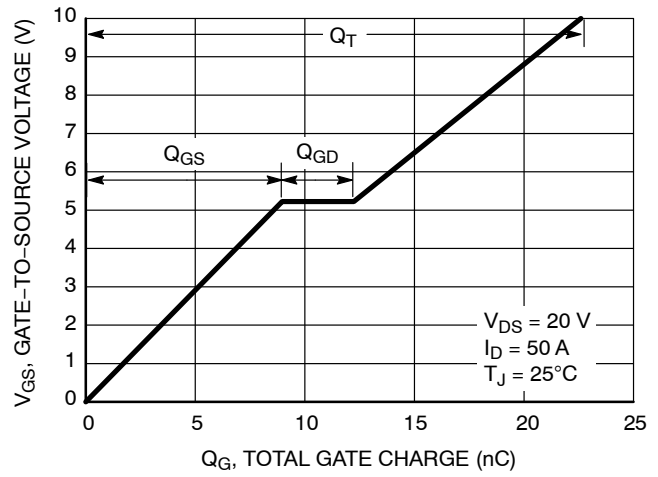


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

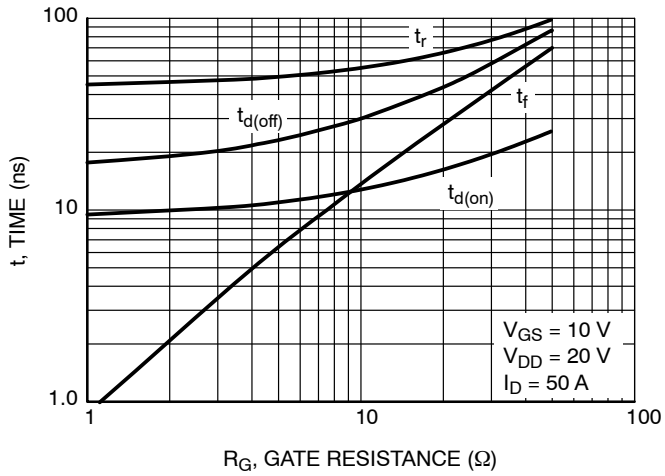


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

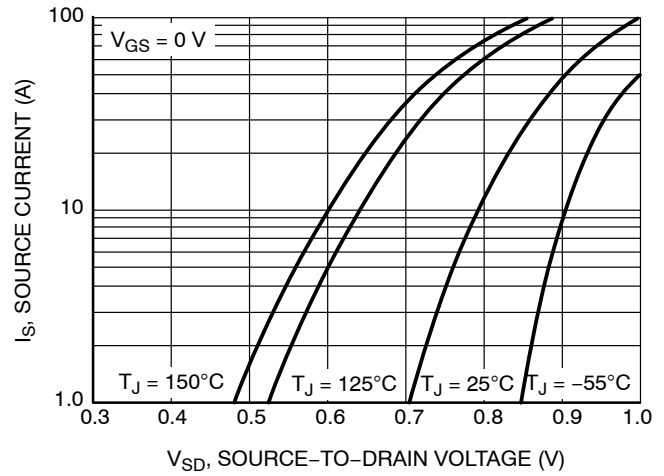


Figure 10. Diode Forward Voltage vs. Current

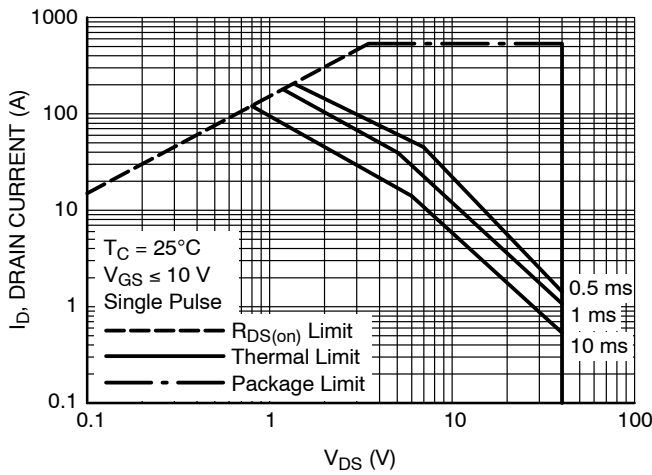


Figure 11. Safe Operating Area

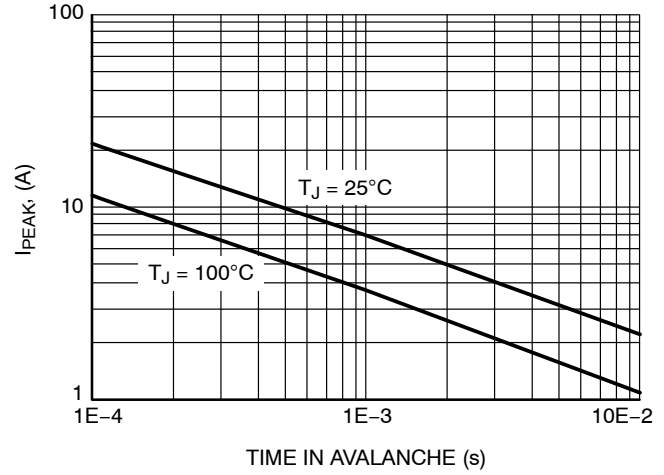


Figure 12.  $I_{PEAK}$  vs. Time in Avalanche

# NTMYS3D5N04C

## TYPICAL CHARACTERISTICS (continued)

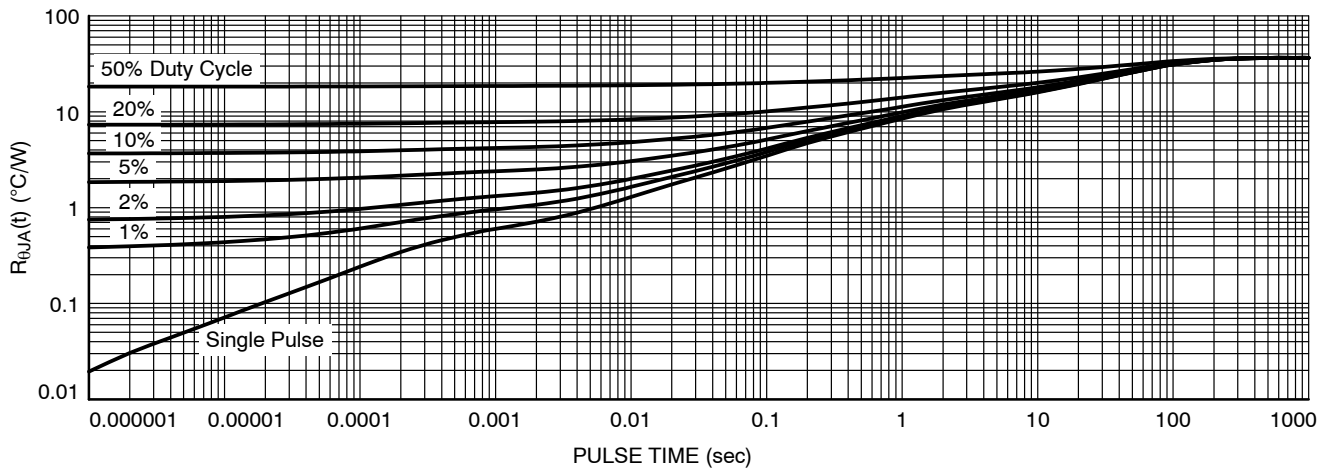


Figure 13. Thermal Characteristics

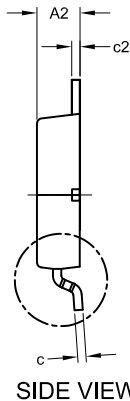
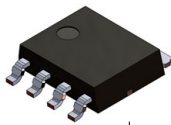
### DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
NTMYS3D5N04CTWG	3D5N04C	LFPAK4 (Pb-Free)	3,000 / Tape & Reel

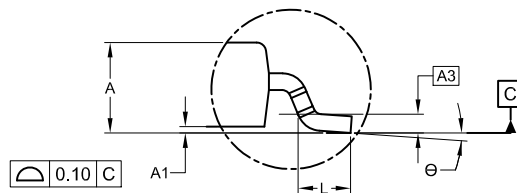
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

**LFPK4 4.90x4.15x1.15MM, 1.27P**  
**CASE 760AB**  
**ISSUE D**

DATE 22 MAY 2024


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.


**DETAIL 'A'**  
SCALE: 2:1

**BOTTOM VIEW**

**RECOMMENDED LAND PATTERN**

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM\***


XXXXXX = Specific Device Code  
A = Assembly Location  
WL = Wafer Lot  
Y = Year  
W = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Some products may not follow the Generic Marking.

MILLIMETER			
DIM	MIN	NOM	MAX
A	1.10	1.20	1.30
A1	0.00	0.08	0.15
A2	1.10	1.15	1.20
A3	0.25 BSC		
b	0.40	0.45	0.50
b2	3.80	4.10	4.40
b4	0.45	0.55	0.65
c	0.19	0.22	0.25
c2	0.19	0.22	0.25
D	4.15 BSC		
D1	3.80	4.00	4.20
D2	3.00	3.10	3.20
D3	0.30	0.40	0.50
D4	0.90	1.00	1.10
D5	0.70	0.80	0.90
D6	0.55	0.65	0.75
D7	0.31 REF		
D8	0.40 REF		
E	4.90 BSC		
E1	4.85	4.95	5.05
E2	3.10	3.20	3.30
E3	0.00	0.10	0.20
E4	2.00	2.10	2.20
e	1.27 BSC		
e/2	0.635 BSC		
e1	0.40 REF		
H	6.00	6.15	6.30
L	0.50	0.70	0.90
L1	0.80	0.90	1.00
L2	1.10 REF		
Θ	0°	4°	8°

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**DESCRIPTION:** LFPK4 4.90x4.15x1.15MM, 1.27P

**PAGE 1 OF 1**

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